4080K/J

40V N-Channel Trench Power MOSFET

40V, 80A

RDS(ON)=6.8mΩ (Typ.) @ VGS = 10V

RDS(ON)=9.5mΩ (Typ.) @ VGS = 4.5V

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Features

- High Density Cell Design for Ultra Low RDS(ON)
- Fully Characterized Avalanche Voltage and Current
- Good Stability and Uniformity with High EAS
- Excellent Package for Good Heat Dissipation

Package



TO-252

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Absolute Maximum Ratings (T_C=25℃unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	TC = 25℃	80	A
		TC = 100℃	42	A
I_{DM}	Pulsed Drain Current		210	A
E_{AS}	Single Pulsed Avalanche Energy		106	J
P_D	Power Dissipation	TC = 25℃	42	W
			0.55	W/℃
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.8	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

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